



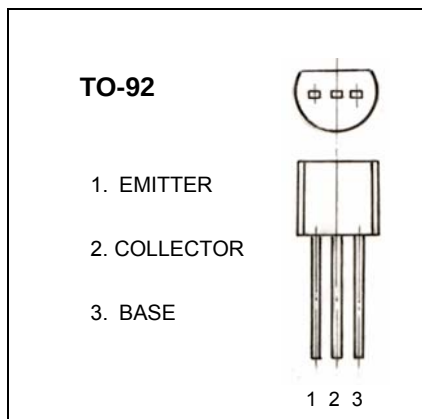
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SA1980 TRANSISTOR (PNP)

FEATURES

- Low collector saturation voltage: $V_{CE(sat)} = -0.3V(\text{Max.})$
- Low output capacitance : $C_{ob} = 4pF(\text{Typ.})$
- Complementary pair with 2SC5343



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Power Dissipation	625	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4	7	pF
Noise figure	NF	$V_{CE} = -6V, I_C = -0.1mA, f = 1KHz, R_S = 10K\Omega$			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	G	L
Range	70-140	120-240	200-400	300-700

Typical Characteristics

2SA1980

Fig. 1 P_C - T_a

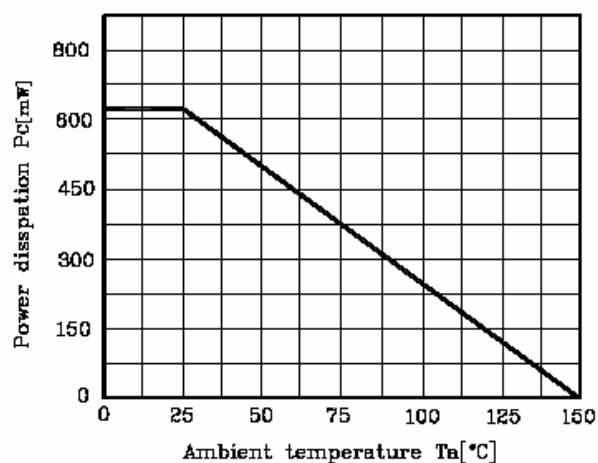


Fig. 2 I_C - V_{BE}

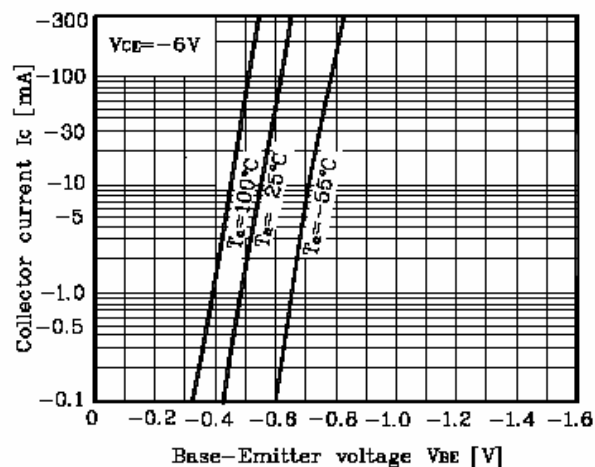


Fig. 3 I_C - V_{CE}

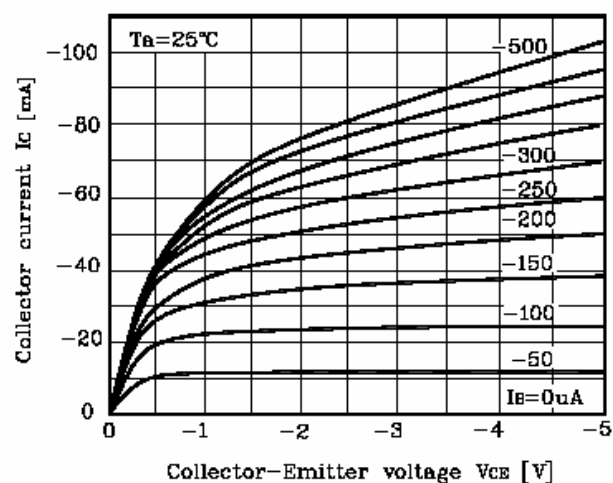


Fig. 4 h_{FE} - I_C

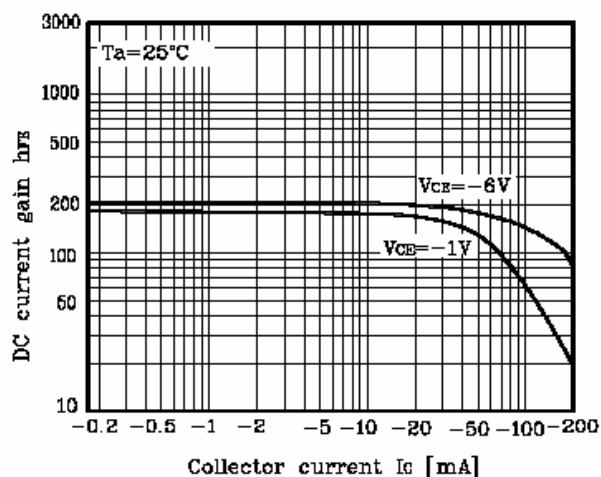


Fig. 5 $V_{CE(sat)}$ - I_C

